

Amendments to the Claims

This listing of claims will replace all prior versions, and listings of claims in the application:

Listing of Claims:

Claim 1 (Currently Amended): A method for manufacturing a semiconductor device, comprising the following steps of, upon processing a wafer ~~to have~~ having a support substrate, a buried oxide supporting body and an intermediate insulating film provided over the whole an entire upper surface of the support substrate, a silicon on insulator layer provided over an entire upper surface of the buried oxide film, and an intermediate insulating film provided over an entire upper surface of the silicon on insulator layer ~~supporting body~~ to thereby fabricate the semiconductor device:

(a) removing a layered portion of the intermediate insulating film, the silicon on insulator layer and the buried oxide film ~~which is~~ provided on a wafer edge region lying around the wafer, by etching using a resist pattern to thereby expose an edge surface region of the support substrate ~~supporting body~~, which corresponds to the wafer edge region; and

(b) forming a conductive layer by sputtering so as to cover said exposed edge surface region and the ~~remaining~~ intermediate insulating film ~~from the upper side~~.

Claim 2 (Currently Amended): [[A]] The method according to claim 1, wherein [[said]]

the resist pattern is formed ~~forming step includes, as steps~~ prior to said step (a) as including,

a step for forming a resist film over ~~[[the]]~~ an entire upper surface of the intermediate insulating film,

a step for effecting a peripheral exposure on a resist film edge region corresponding to the wafer edge region, ~~of the resist film~~ by using a peripheral exposure function of an exposure system, and

a step for removing the resist film edge region subjected to the peripheral exposure.

Claim 3 (Currently Amended): ~~[[A]]~~ The method according to claim 1, wherein ~~[[said]]~~ the resist pattern is formed ~~forming step includes, as steps~~ prior to said step (a) as including,

a step for forming a resist film over ~~[[the]]~~ an entire upper surface of the intermediate insulating film, and

a step for applying chemicals onto ~~[[the]]~~ an upper surface of the resist film by a spin coating apparatus to remove ~~[[the]]~~ a resist film edge region corresponding to the wafer edge region~~[[,]] of the resist film.~~

Claim 4 (Currently Amended): ~~[[A]]~~ The method according to claim 1, wherein the support substrate ~~supporting body~~ is formed of a ~~material selected from a~~

semiconductor material and a conductive material.

Claim 5 (Currently Amended): ~~[[A]]~~ The method according to claim 2, wherein the support substrate ~~supporting body~~ is formed of a ~~material selected from a~~ semiconductor material and a conductive material.

Claim 6 (Currently Amended): ~~[[A]]~~ The method according to claim 3, wherein the support substrate ~~supporting body~~ is formed of a ~~material selected from a~~ semiconductor material and a conductive material.

Claim 7 (New): A method of manufacturing a semiconductor device comprising:

providing an SOI wafer as having a substrate, an oxide film on the substrate, and a silicon layer on the oxide film;

forming a gate element on the silicon layer;

depositing an insulating layer over the gate element and the silicon layer;

forming a contact through the insulating layer to the gate element, the contact being exposed at a surface of the insulating layer;

removing the insulating layer, the silicon layer and the oxide film from an edge region of the SOI wafer, to thereby expose an edge surface region of the substrate; and

sputtering a conductive layer on the insulating layer, the contact exposed at the surface of the insulating layer, and the edge surface region of the substrate.

Claim 8 (New): The method of manufacturing a semiconductor device of claim 7, wherein said removing the insulating layer, the silicon layer and the oxide film comprises:

forming a resist layer on an entirety of the surface of the insulating layer and on the contact exposed at the surface of the insulating layer;
peripherally exposing an edge region of the resist layer; and
removing the exposed region of the resist layer to form a patterned resist.

Claim 9 (New): The method of manufacturing a semiconductor device of claim 8, wherein said removing the insulating layer, the silicon layer and the oxide film further comprises etching using the patterned resist as a mask.

Claim 10 (New): The method of manufacturing a semiconductor device of claim 7, wherein said removing the insulating layer, the silicon layer and the oxide film comprises:

forming a resist layer on an entirety of the surface of the insulating layer and on the contact exposed at the surface of the insulating layer; and
spin coating chemicals onto the surface of the insulating layer to remove an edge region of the resist layer above the edge surface region of the substrate and form a patterned resist.

Claim 11 (New): The method of manufacturing a semiconductor device of claim 10, wherein said removing the insulating layer, the silicon layer and the oxide film further comprises etching using the patterned resist as a mask.

Claim 12 (New): The method of manufacturing a semiconductor device of claim 7, wherein the substrate is a semiconductor layer.

Claim 13 (New): The method of manufacturing a semiconductor device of claim 7, wherein said forming a gate element comprises:

- forming a gate insulating film on the silicon layer; and
- forming a gate electrode on the gate insulating film.